

MUN5211DW1T1G Series

Preferred Devices

Dual Bias Resistor Transistors

NPN Silicon Surface Mount Transistors with Monolithic Bias Resistor Network

The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. These digital transistors are designed to replace a single device and its external resistor bias network. The BRT eliminates these individual components by integrating them into a single device. In the MUN5211DW1T1G series, two BRT devices are housed in the SOT-363 package which is ideal for low power surface mount applications where board space is at a premium.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

(T_A = 25°C unless otherwise noted, common for Q₁ and Q₂)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Collector Current	I _C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation T _A = 25°C Derate above 25°C	P _D	187 (Note 1) 256 (Note 2) 1.5 (Note 1) 2.0 (Note 2)	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA}	670 (Note 1) 490 (Note 2)	°C/W
Characteristic (Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation T _A = 25°C Derate above 25°C	P _D	250 (Note 1) 385 (Note 2) 2.0 (Note 1) 3.0 (Note 2)	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA}	493 (Note 1) 325 (Note 2)	°C/W
Thermal Resistance, Junction-to-Lead	R _{θJL}	188 (Note 1) 208 (Note 2)	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

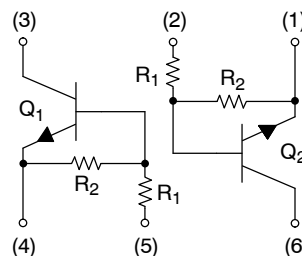
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-4 @ Minimum Pad
2. FR-4 @ 1.0 x 1.0 inch Pad



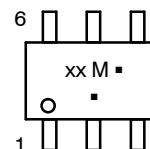
ON Semiconductor®

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SOT-363
CASE 419B
STYLE 1

MARKING DIAGRAM



xx = Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

DEVICE MARKING INFORMATION

See specific marking information in the device marking table on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

MUN5211DW1T1G Series

DEVICE MARKING AND RESISTOR VALUES

Device	Package	Marking	R1 (K)	R2 (K)	Shipping†
MUN5211DW1T1G	SOT-363 (Pb-Free)	7A	10	10	3000 / Tape & Reel
MUN5212DW1T1G	SOT-363 (Pb-Free)	7B	22	22	3000 / Tape & Reel
MUN5213DW1T1G	SOT-363 (Pb-Free)	7C	47	47	3000 / Tape & Reel
MUN5214DW1T1G	SOT-363 (Pb-Free)	7D	10	47	3000 / Tape & Reel
MUN5215DW1T1G	SOT-363 (Pb-Free)	7E	10	∞	3000 / Tape & Reel
MUN5216DW1T1G	SOT-363 (Pb-Free)	7F	4.7	∞	3000 / Tape & Reel
MUN5230DW1T1G	SOT-363 (Pb-Free)	7G	1.0	1.0	3000 / Tape & Reel
MUN5231DW1T1G	SOT-363 (Pb-Free)	7H	2.2	2.2	3000 / Tape & Reel
MUN5232DW1T1G	SOT-363 (Pb-Free)	7J	4.7	4.7	3000 / Tape & Reel
MUN5233DW1T1G	SOT-363 (Pb-Free)	7K	4.7	47	3000 / Tape & Reel
MUN5234DW1T1G	SOT-363 (Pb-Free)	7L	22	47	3000 / Tape & Reel
MUN5235DW1T1G	SOT-363 (Pb-Free)	7M	2.2	47	3000 / Tape & Reel
MUN5236DW1T1G	SOT-363 (Pb-Free)	7N	100	100	3000 / Tape & Reel
MUN5237DW1T1G	SOT-363 (Pb-Free)	7P	47	22	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MUN5211DW1T1G Series

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted, common for Q₁ and Q₂)

Characteristic	Symbol	Min	Typ	Max	Unit	
OFF CHARACTERISTICS						
Collector-Base Cutoff Current ($V_{CB} = 50\text{ V}$, $I_E = 0$)	I_{CBO}	–	–	100	nAdc	
Collector-Emitter Cutoff Current ($V_{CE} = 50\text{ V}$, $I_B = 0$)	I_{CEO}	–	–	500	nAdc	
Emitter-Base Cutoff Current ($V_{EB} = 6.0\text{ V}$, $I_C = 0$)	MUN5211DW1T1G	I_{EBO}	–	–	0.5	mAdc
	MUN5212DW1T1G		–	–	0.2	
	MUN5213DW1T1G		–	–	0.1	
	MUN5214DW1T1G		–	–	0.2	
	MUN5215DW1T1G		–	–	0.9	
	MUN5216DW1T1G		–	–	1.9	
	MUN5230DW1T1G		–	–	4.3	
	MUN5231DW1T1G		–	–	2.3	
	MUN5232DW1T1G		–	–	1.5	
	MUN5233DW1T1G		–	–	0.18	
	MUN5234DW1T1G		–	–	0.13	
	MUN5235DW1T1G		–	–	0.2	
	MUN5236DW1T1G		–	–	0.05	
	MUN5237DW1T1G		–	–	0.13	
Collector-Base Breakdown Voltage ($I_C = 10\text{ }\mu\text{A}$, $I_E = 0$)	$V_{(BR)CBO}$	50	–	–	Vdc	
Collector-Emitter Breakdown Voltage (Note 3) ($I_C = 2.0\text{ mA}$, $I_B = 0$)	$V_{(BR)CEO}$	50	–	–	Vdc	

3. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%

MUN5211DW1T1G Series

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted, common for Q₁ and Q₂)

Characteristic		Symbol	Min	Typ	Max	Unit		
ON CHARACTERISTICS (Note 4)								
DC Current Gain (V _{CE} = 10 V, I _C = 5.0 mA)	MUN5211DW1T1G MUN5212DW1T1G MUN5213DW1T1G MUN5214DW1T1G MUN5215DW1T1G MUN5216DW1T1G MUN5230DW1T1G MUN5231DW1T1G MUN5232DW1T1G MUN5233DW1T1G MUN5234DW1T1G MUN5235DW1T1G MUN5236DW1T1G MUN5237DW1T1G	h _{FE}	35 60 80 80 160 160 3.0 8.0 15 80 80 80 80 80	60 100 140 140 350 350 5.0 15 30 200 150 140 150 140	– – – – – – – – – – – – – –			
Collector-Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.3 mA)	MUN5211DW1T1G MUN5212DW1T1G MUN5213DW1T1G MUN5214DW1T1G MUN5235DW1T1G MUN5236DW1T1G	V _{CE(sat)}	– – – – – –	– – – – – –	0.25 0.25 0.25 0.25 0.25 0.25	Vdc		
(I _C = 10 mA, I _B = 5 mA)	MUN5230DW1T1G MUN5231DW1T1G MUN5237DW1T1G		– – –	– – –	0.25 0.25 0.25			
(I _C = 10 mA, I _B = 1 mA)	MUN5215DW1T1G MUN5216DW1T1G MUN5232DW1T1G MUN5233DW1T1G MUN5234DW1T1G		– – – – –	– – – – –	0.25 0.25 0.25 0.25 0.25			
Output Voltage (on) (V _{CC} = 5.0 V, V _B = 2.5 V, R _L = 1.0 kΩ)	MUN5211DW1T1G MUN5212DW1T1G MUN5214DW1T1G MUN5215DW1T1G MUN5216DW1T1G MUN5230DW1T1G MUN5231DW1T1G MUN5232DW1T1G MUN5233DW1T1G MUN5234DW1T1G MUN5235DW1T1G		V _{OL}	– – – – – – – – – – –	– – – – – – – – – – –		0.2 0.2 0.2 0.2 0.2 0.2 0.2 0.2 0.2 0.2 0.2	Vdc
(V _{CC} = 5.0 V, V _B = 3.5 V, R _L = 1.0 kΩ)	MUN5213DW1T1G			–	–		0.2	
(V _{CC} = 5.0 V, V _B = 5.5 V, R _L = 1.0 kΩ)	MUN5236DW1T1G			–	–		0.2	
(V _{CC} = 5.0 V, V _B = 4.0 V, R _L = 1.0 kΩ)	MUN5237DW1T1G			–	–		0.2	

4. Pulse Test: Pulse Width < 300 μs, Duty Cycle < 2.0%

MUN5211DW1T1G Series

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted, common for Q₁ and Q₂) (Continued)

Characteristic		Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS (Note 5) (Continued)						
Output Voltage (off) (V _{CC} = 5.0 V, V _B = 0.5 V, R _L = 1.0 kΩ)	MUN5211DW1T1G	V _{OH}	4.9	–	–	V _{dc}
	MUN5212DW1T1G		4.9	–	–	
	MUN5213DW1T1G		4.9	–	–	
	MUN5214DW1T1G		4.9	–	–	
	MUN5233DW1T1G		4.9	–	–	
	MUN5234DW1T1G		4.9	–	–	
	MUN5235DW1T1G		4.9	–	–	
(V _{CC} = 5.0 V, V _B = 0.050 V, R _L = 1.0 kΩ)	MUN5230DW1T1G		4.9	–	–	
(V _{CC} = 5.0 V, V _B = 0.25 V, R _L = 1.0 kΩ)	MUN5215DW1T1G		4.9	–	–	
	MUN5216DW1T1G		4.9	–	–	
	MUN5231DW1T1G		4.9	–	–	
	MUN5232DW1T1G		4.9	–	–	
	MUN5236DW1T1G		4.9	–	–	
	MUN5237DW1T1G		4.9	–	–	
Input Resistor	MUN5211DW1T1G	R1	7.0	10	13	k Ω
	MUN5212DW1T1G		15.4	22	28.6	
	MUN5213DW1T1G		32.9	47	61.1	
	MUN5214DW1T1G		7.0	10	13	
	MUN5215DW1T1G		7.0	10	13	
	MUN5216DW1T1G		3.3	4.7	6.1	
	MUN5230DW1T1G		0.7	1.0	1.3	
	MUN5231DW1T1G		1.5	2.2	2.9	
	MUN5232DW1T1G		3.3	4.7	6.1	
	MUN5233DW1T1G		3.3	4.7	6.1	
	MUN5234DW1T1G		15.4	22	28.6	
	MUN5235DW1T1G		1.54	2.2	2.86	
	MUN5236DW1T1G		70	100	130	
	MUN5237DW1T1G		32.9	47	61.1	
Resistor Ratio	MUN5211DW1T1G/MUN5212DW1T1G/ MUN5213DW1T1G/MUN5236DW1T1G MUN5214DW1T1G MUN5215DW1T1G/MUN5216DW1T1G MUN5230DW1T1G/MUN5231DW1T1G/MUN5232DW1T1G MUN5233DW1T1G MUN5234DW1T1G MUN5235DW1T1G MUN5237DW1T1G	R1/R2	0.8 0.17 – 0.8 0.055 0.38 0.038 1.7	1.0 0.21 – 1.0 0.1 0.47 0.047 2.1	1.2 0.25 – 1.2 0.185 0.56 0.056 2.6	

5. Pulse Test: Pulse Width < 300 μs, Duty Cycle < 2.0%

ALL MUN5211DW1T1G SERIES DEVICES

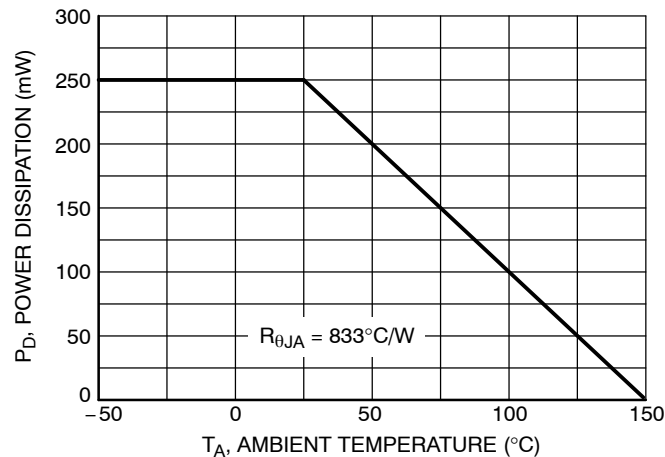


Figure 1. Derating Curve

MUN5211DW1T1G Series

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5211DW1T1G

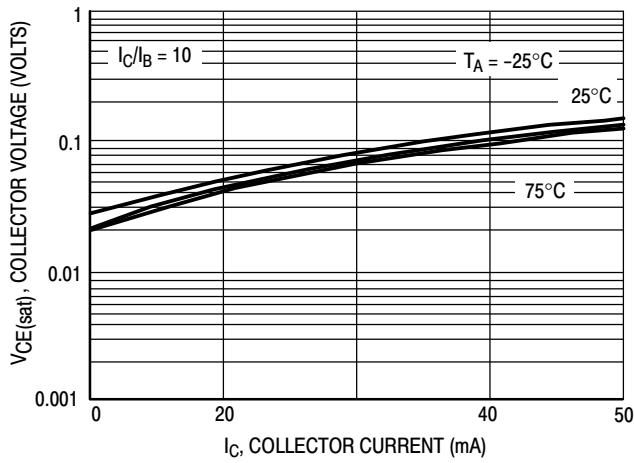


Figure 2. $V_{CE(sat)}$ versus I_C

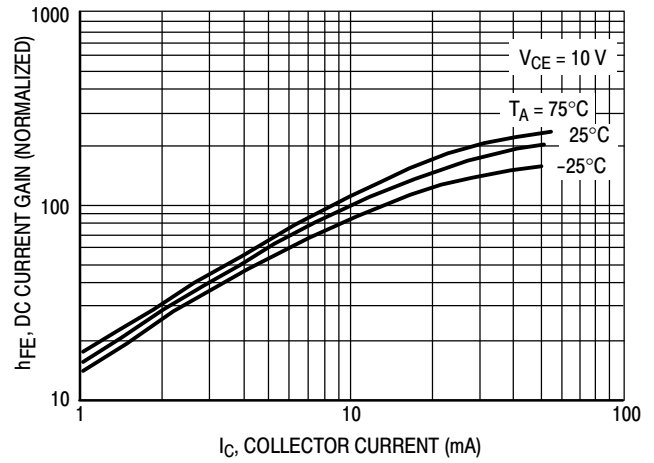


Figure 3. DC Current Gain

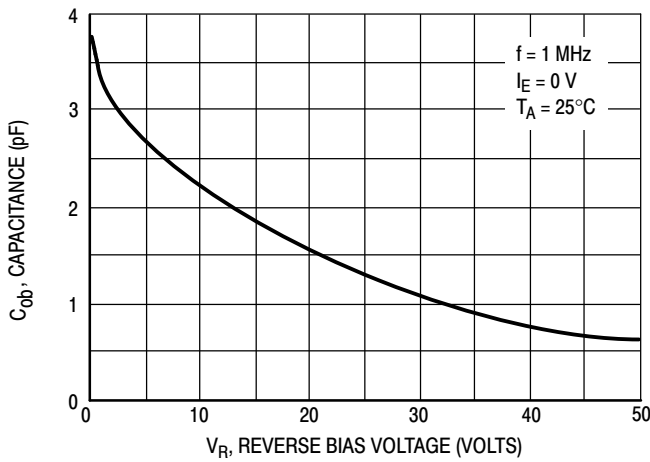


Figure 4. Output Capacitance

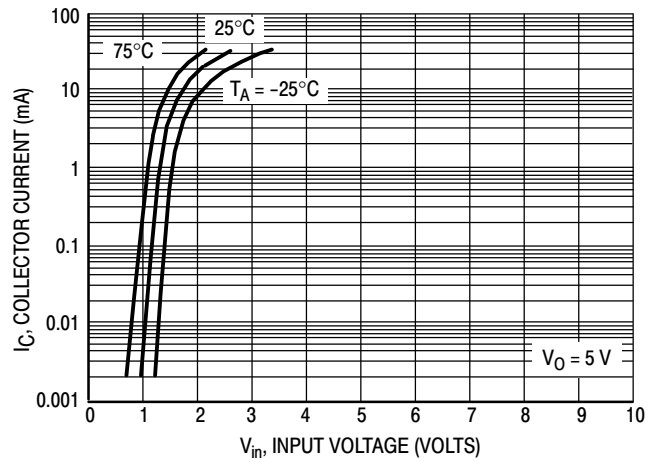


Figure 5. Output Current versus Input Voltage

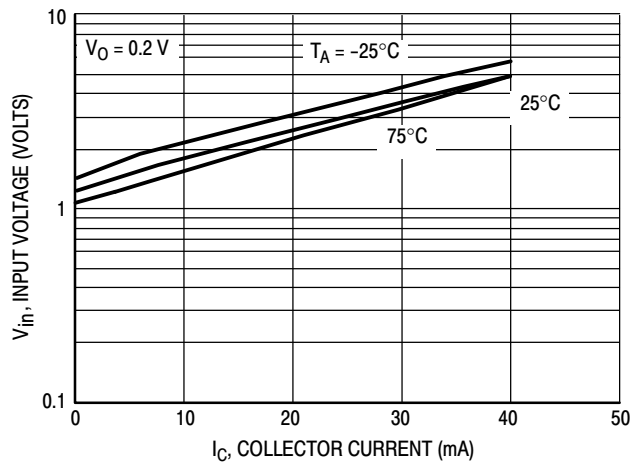


Figure 6. Input Voltage versus Output Current

MUN5211DW1T1G Series

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5212DW1T1G

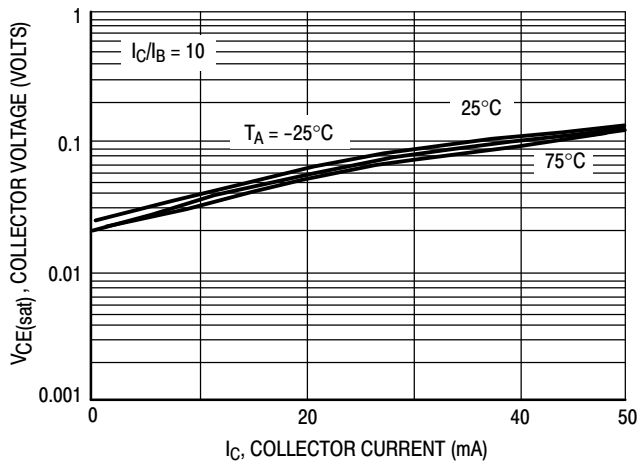


Figure 7. $V_{CE(sat)}$ versus I_C

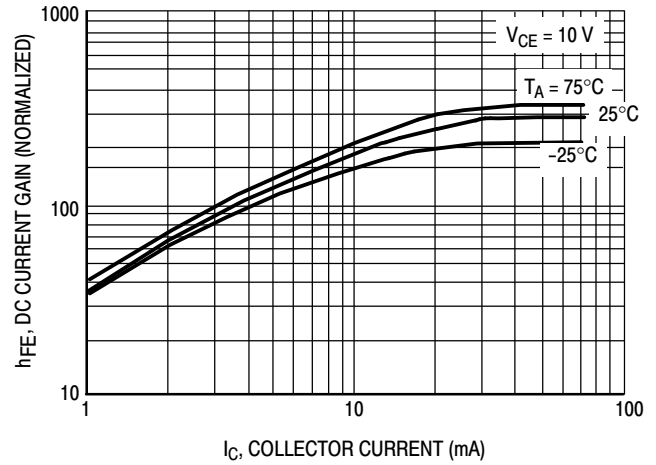


Figure 8. DC Current Gain

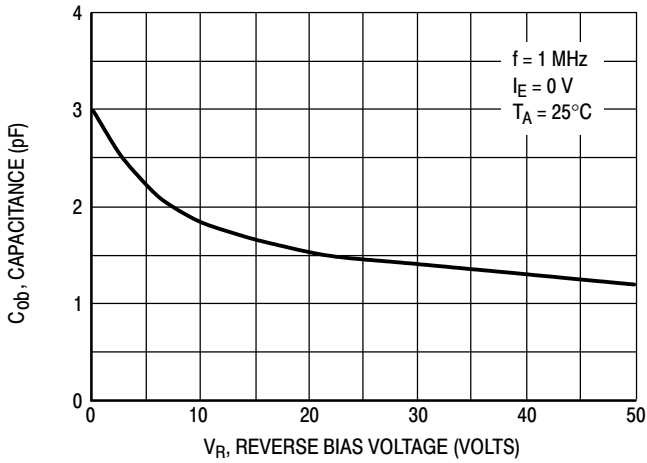


Figure 9. Output Capacitance

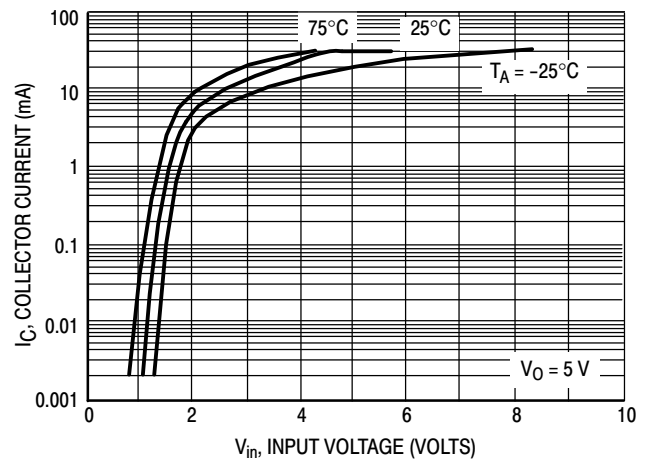


Figure 10. Output Current versus Input Voltage

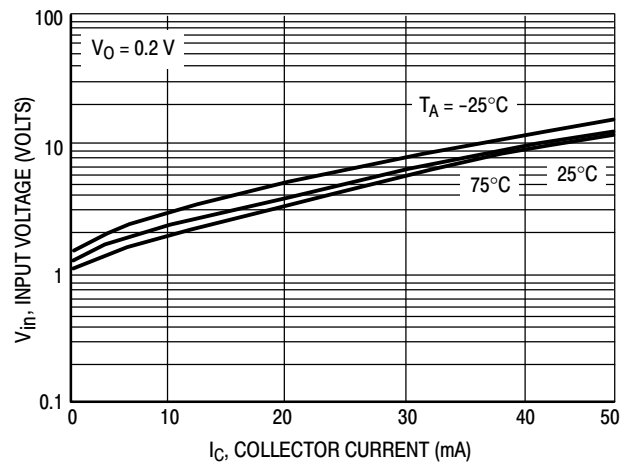


Figure 11. Input Voltage versus Output Current

MUN5211DW1T1G Series

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5213DW1T1G

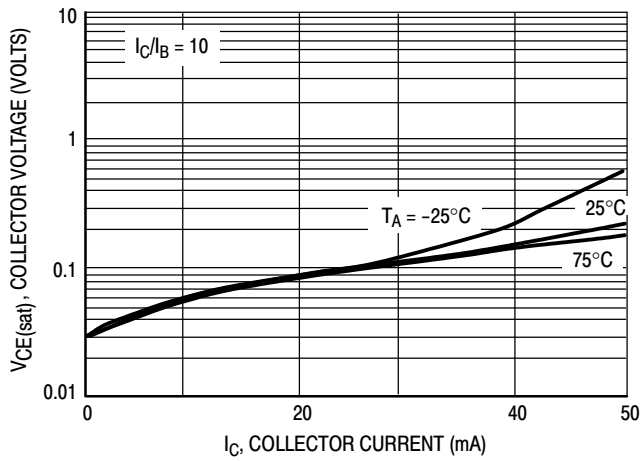


Figure 12. $V_{CE(sat)}$ versus I_C

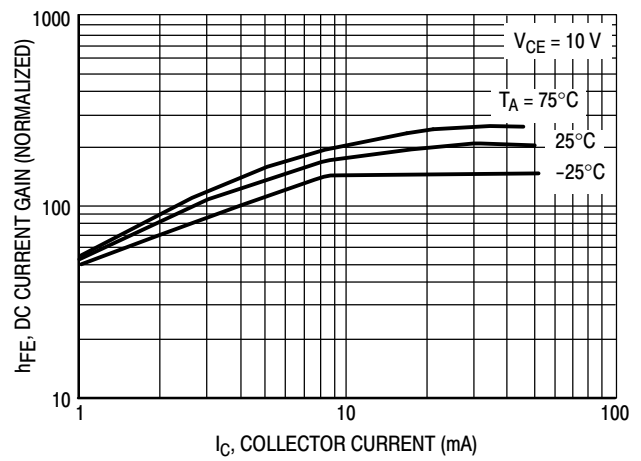


Figure 13. DC Current Gain

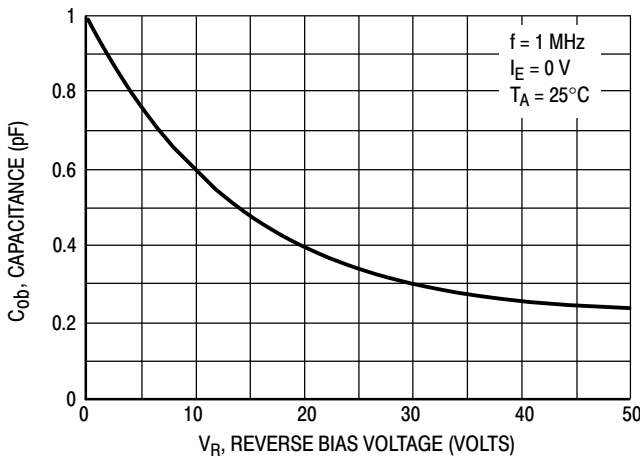


Figure 14. Output Capacitance

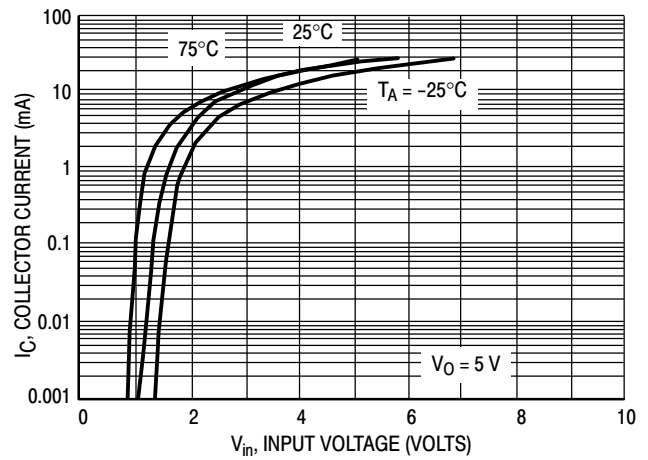


Figure 15. Output Current versus Input Voltage

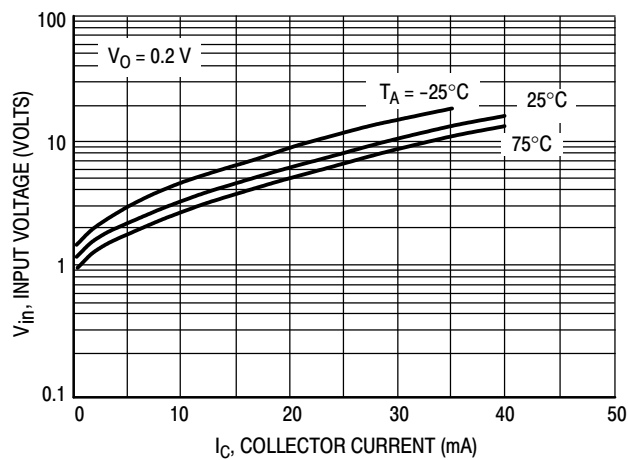


Figure 16. Input Voltage versus Output Current

MUN5211DW1T1G Series

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5214DW1T1G

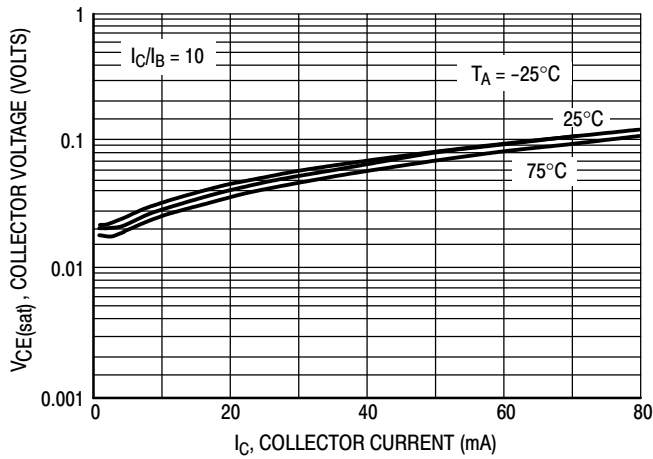


Figure 17. $V_{CE(sat)}$ versus I_C

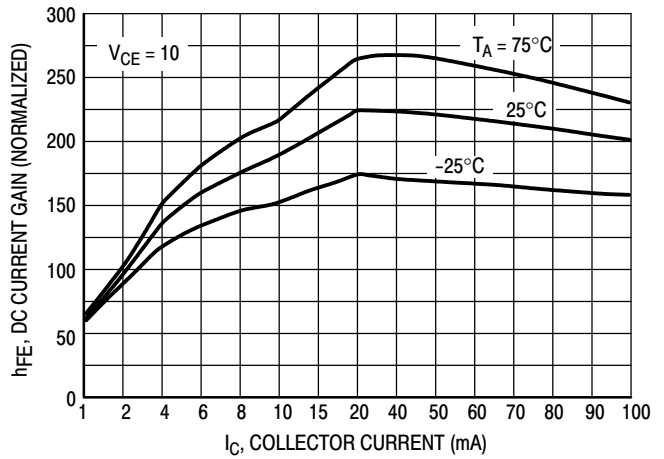


Figure 18. DC Current Gain

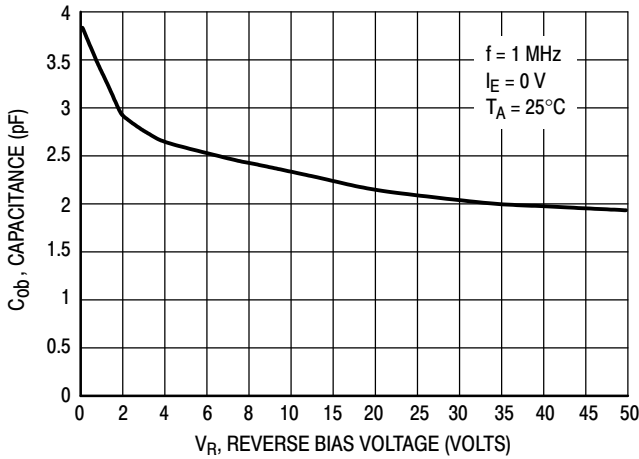


Figure 19. Output Capacitance

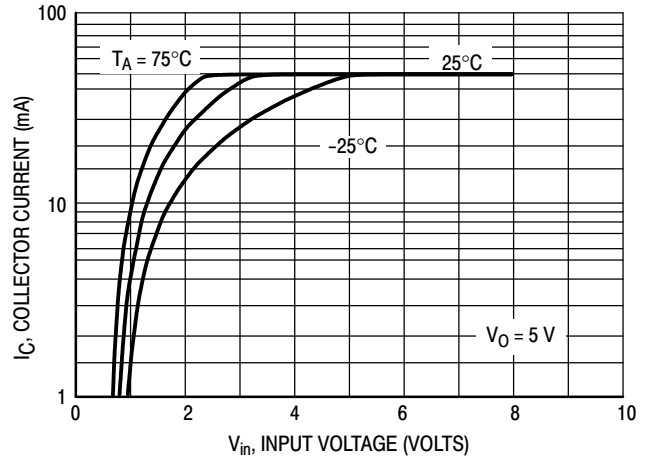


Figure 20. Output Current versus Input Voltage

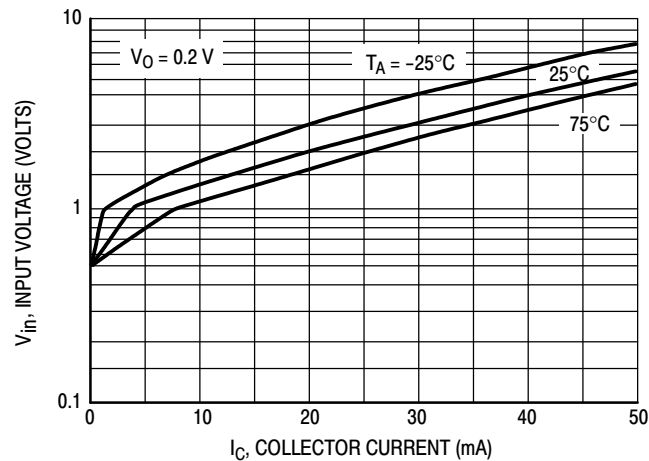


Figure 21. Input Voltage versus Output Current

MUN5211DW1T1G Series

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5215DW1T1G

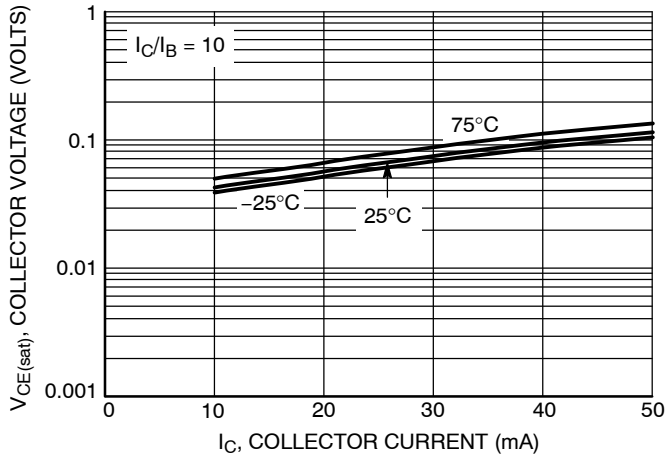


Figure 22. $V_{CE(sat)}$ versus I_C

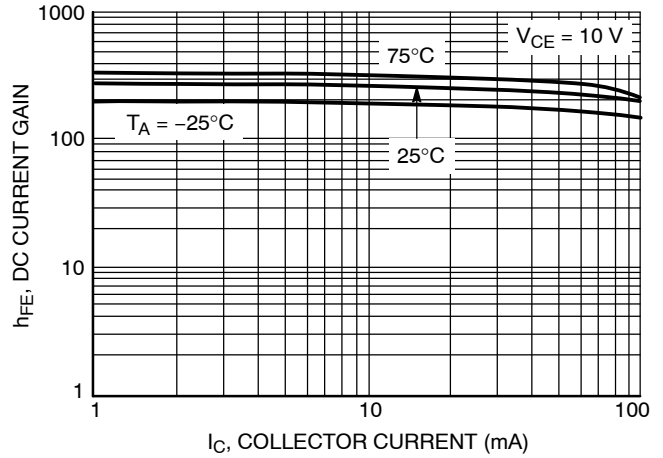


Figure 23. DC Current Gain

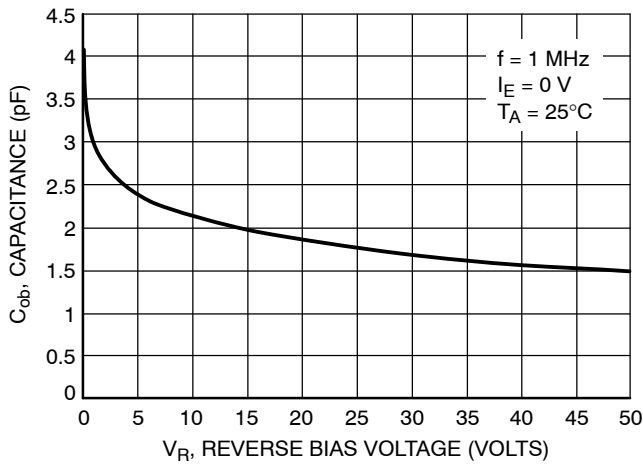


Figure 24. Output Capacitance

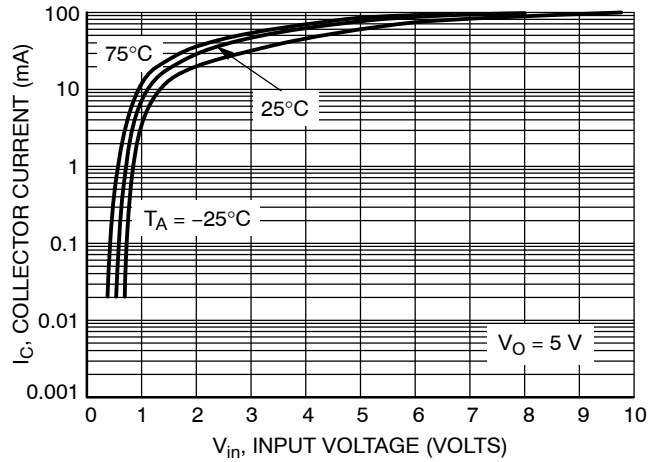


Figure 25. Output Current versus Input Voltage

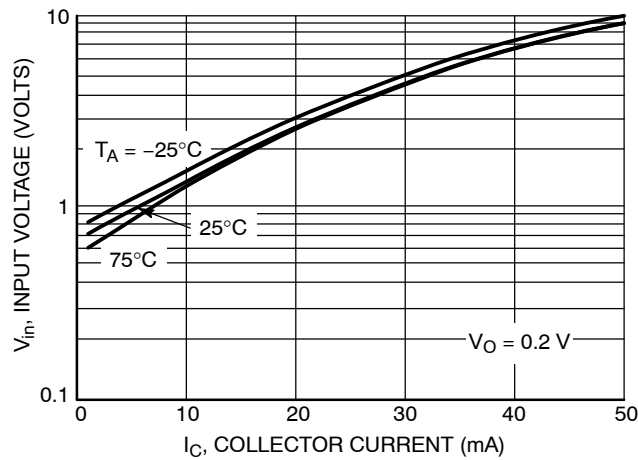


Figure 26. Input Voltage versus Output Current

MUN5211DW1T1G Series

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5216DW1T1G

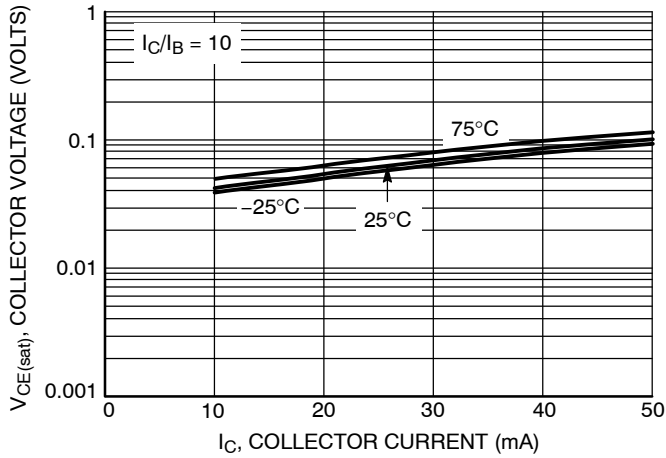


Figure 27. $V_{CE(sat)}$ versus I_C

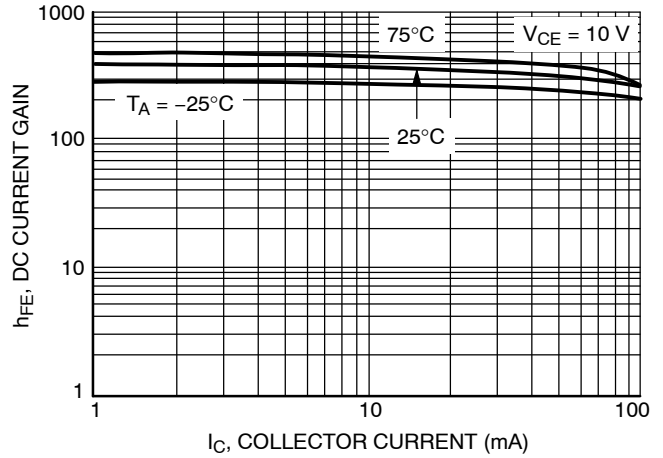


Figure 28. DC Current Gain

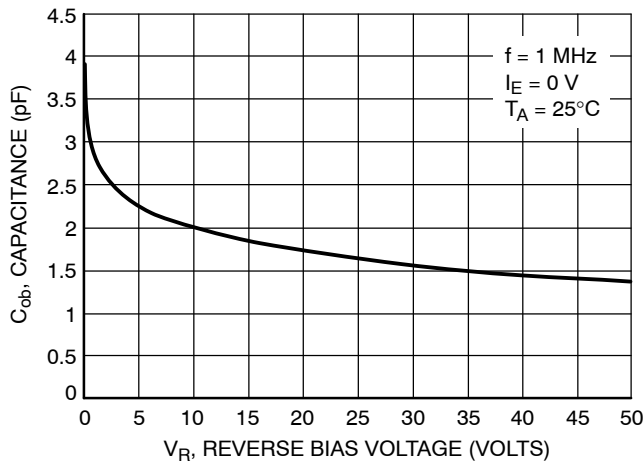


Figure 29. Output Capacitance

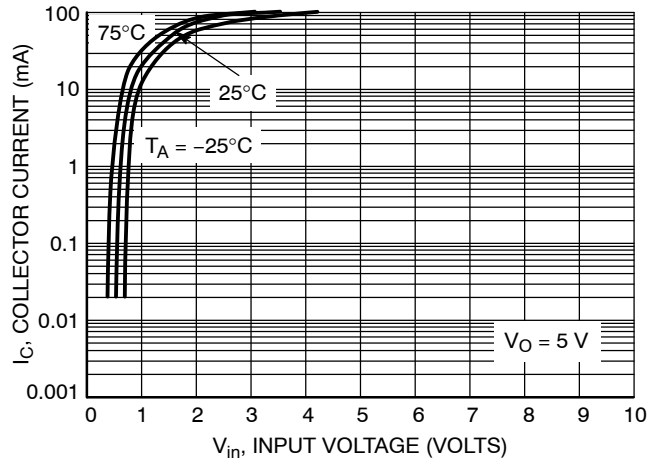


Figure 30. Output Current versus Input Voltage

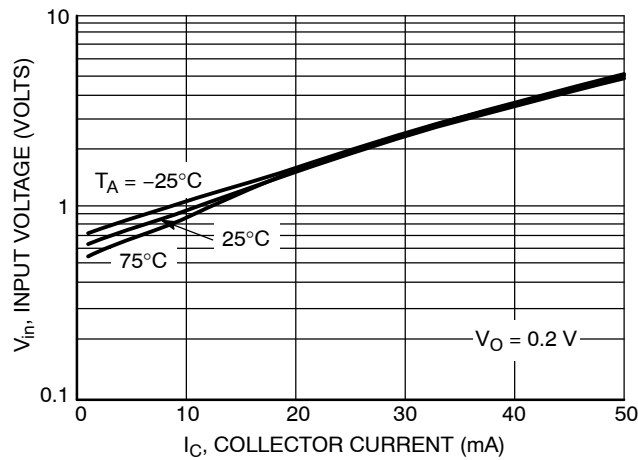


Figure 31. Input Voltage versus Output Current

MUN5211DW1T1G Series

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5230DW1T1G

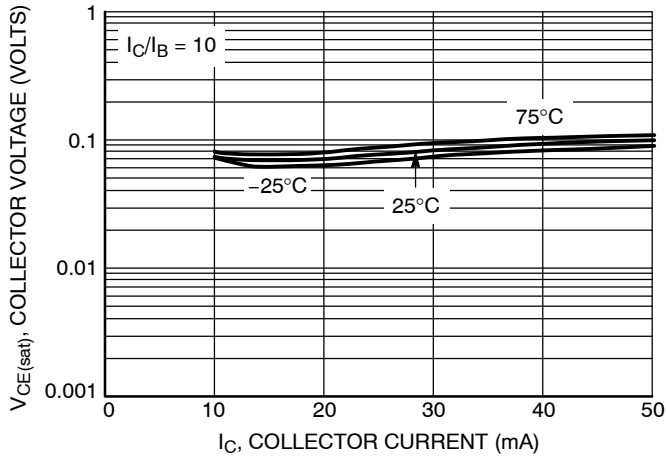


Figure 32. $V_{CE(sat)}$ versus I_C

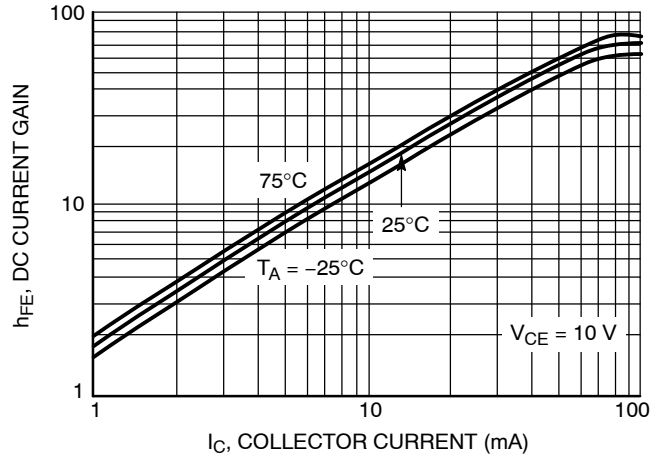


Figure 33. DC Current Gain

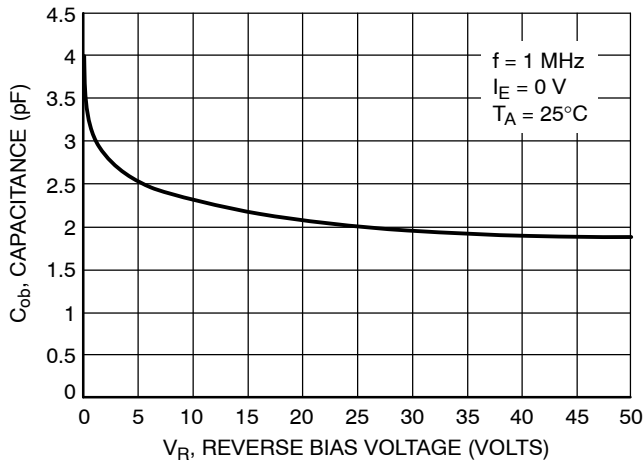


Figure 34. Output Capacitance

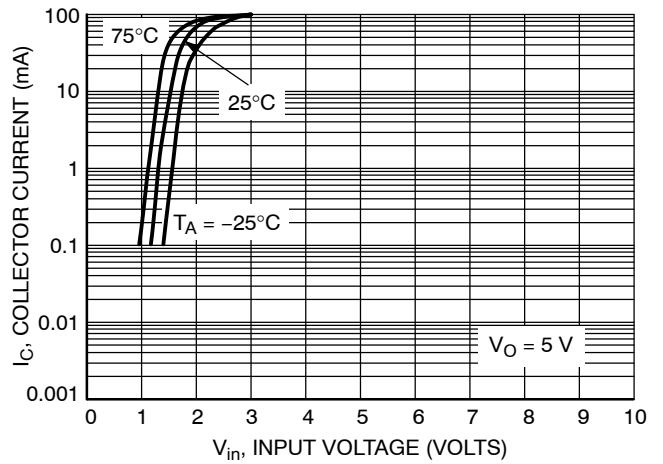


Figure 35. Output Current versus Input Voltage

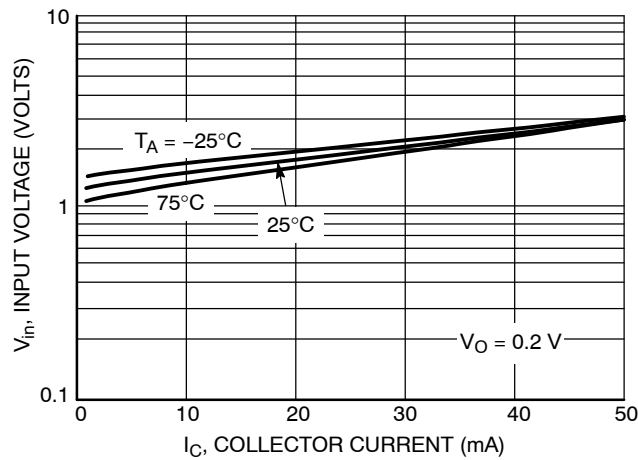


Figure 36. Input Voltage versus Output Current

MUN5211DW1T1G Series

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5231DW1T1G

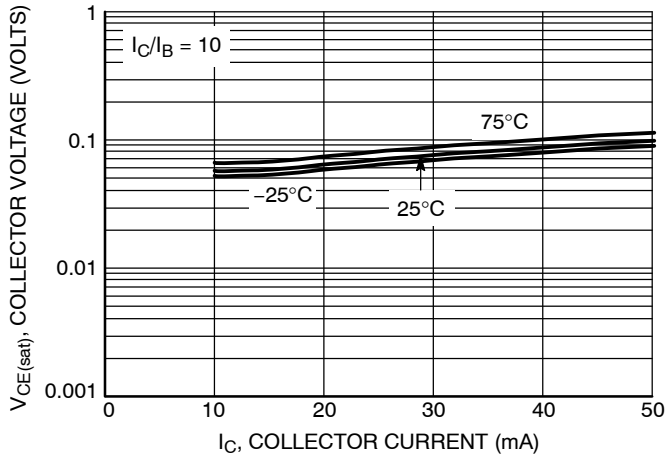


Figure 37. $V_{CE(sat)}$ versus I_C

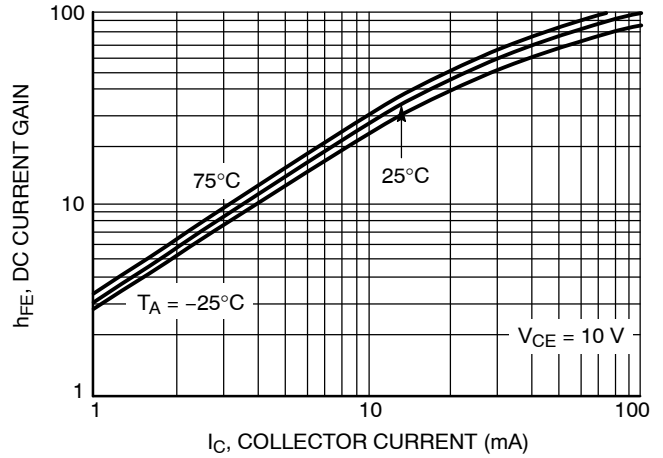


Figure 38. DC Current Gain

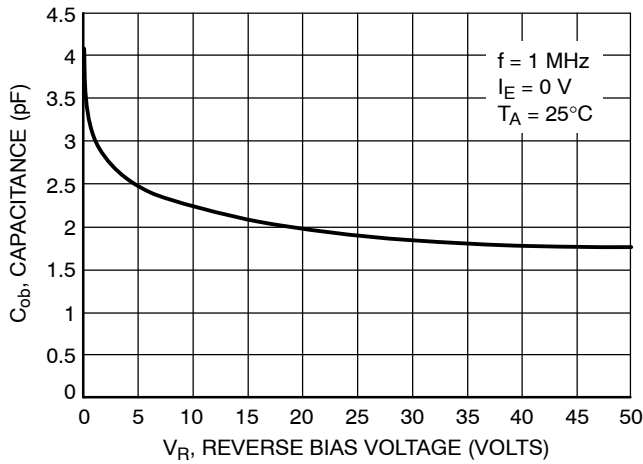


Figure 39. Output Capacitance

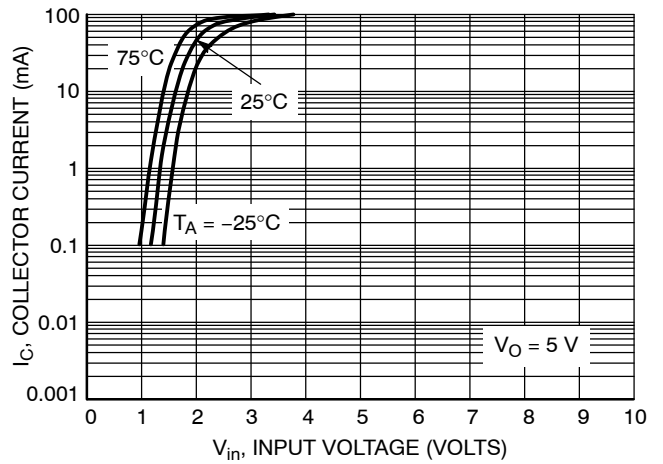


Figure 40. Output Current versus Input Voltage

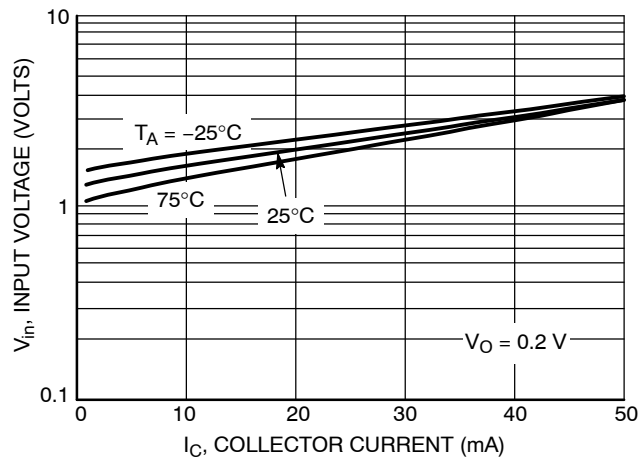


Figure 41. Input Voltage versus Output Current

MUN5211DW1T1G Series

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5232DW1T1G

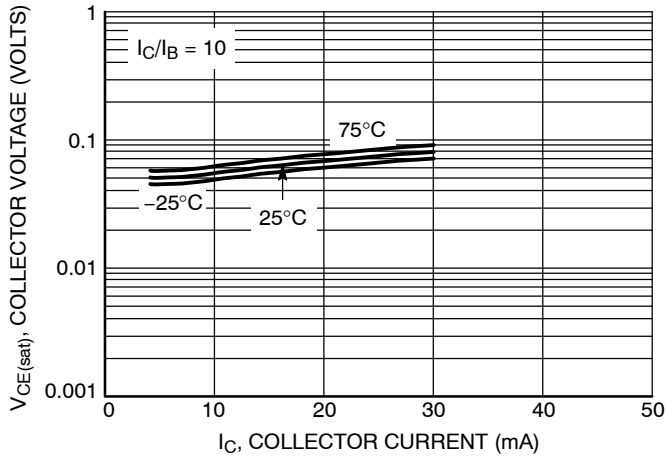


Figure 42. $V_{CE(sat)}$ versus I_C

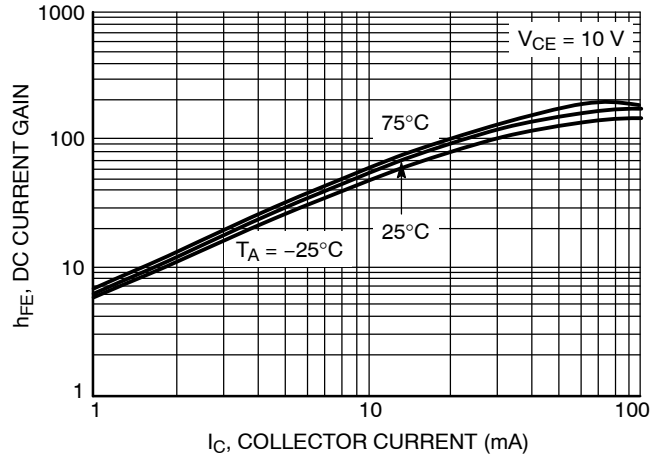


Figure 43. DC Current Gain

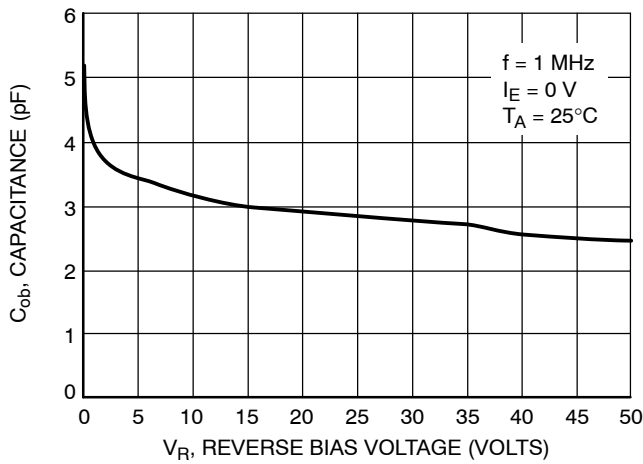


Figure 44. Output Capacitance

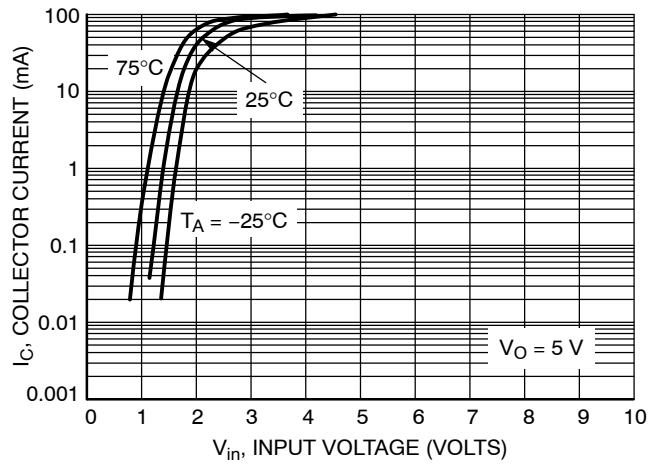


Figure 45. Output Current versus Input Voltage

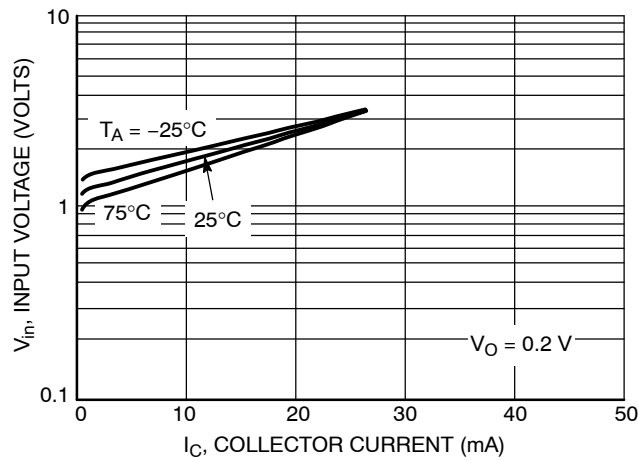


Figure 46. Input Voltage versus Output Current

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5233DW1T1G

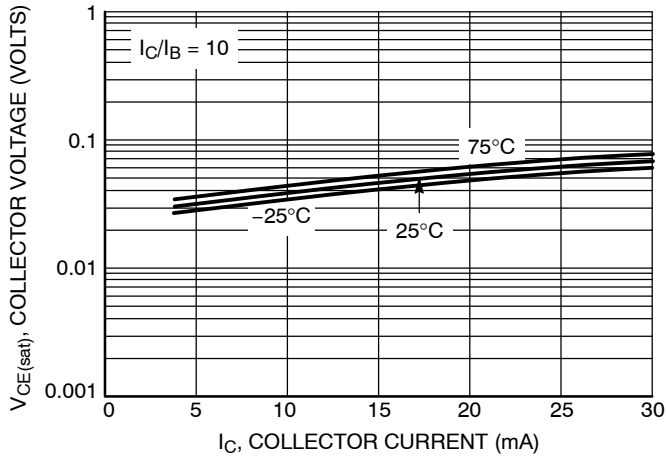


Figure 47. $V_{CE(sat)}$ versus I_C

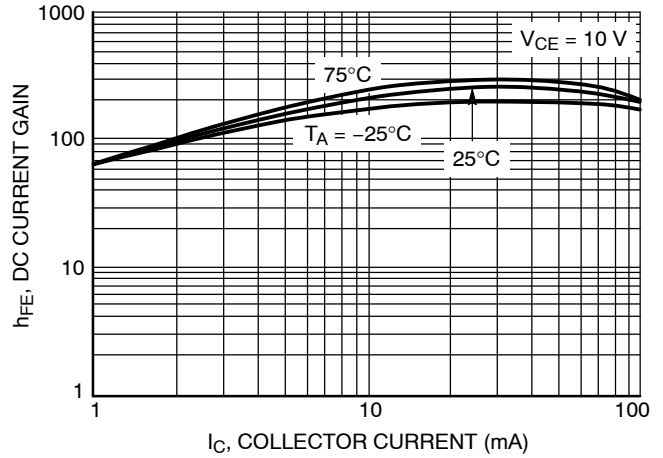


Figure 48. DC Current Gain

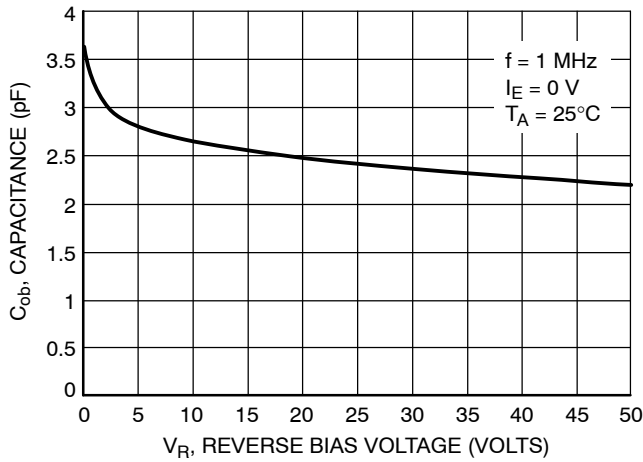


Figure 49. Output Capacitance

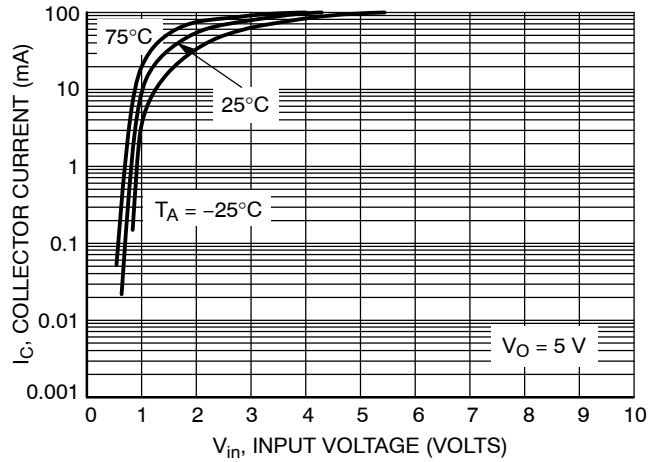


Figure 50. Output Current versus Input Voltage

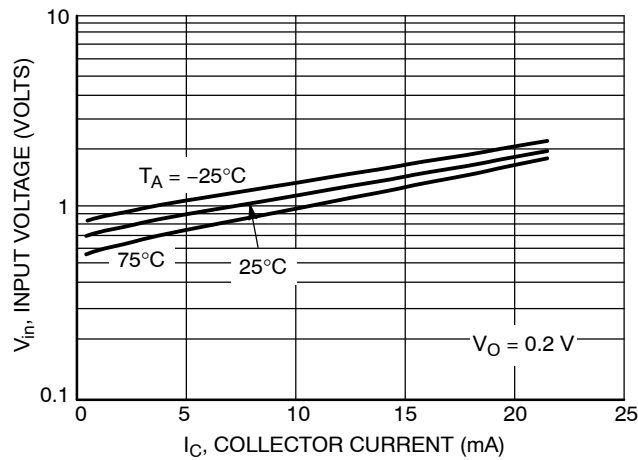


Figure 51. Input Voltage versus Output Current

MUN5211DW1T1G Series

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5234DW1T1G

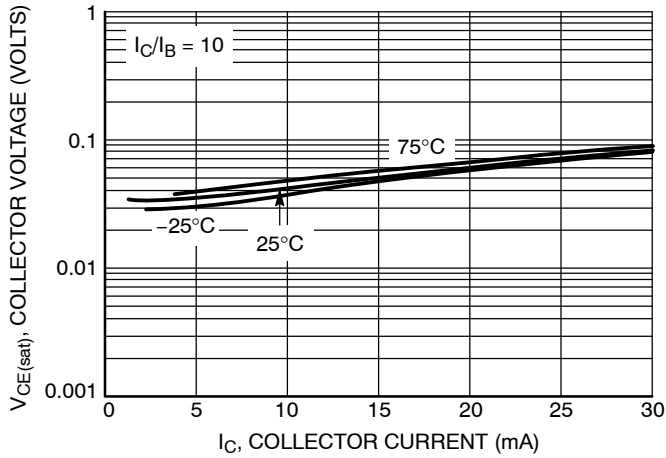


Figure 52. $V_{CE(sat)}$ versus I_C

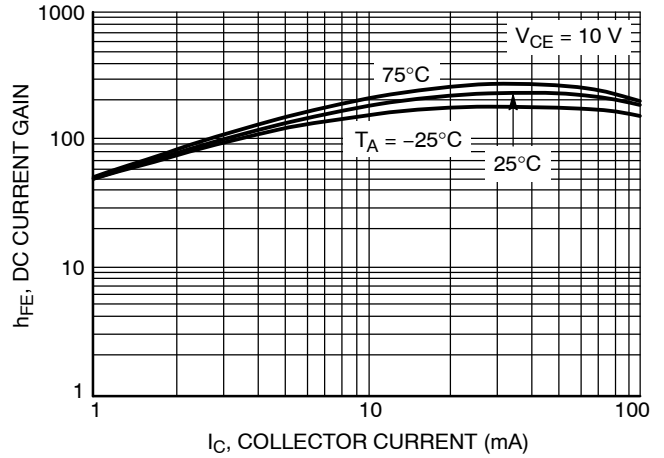
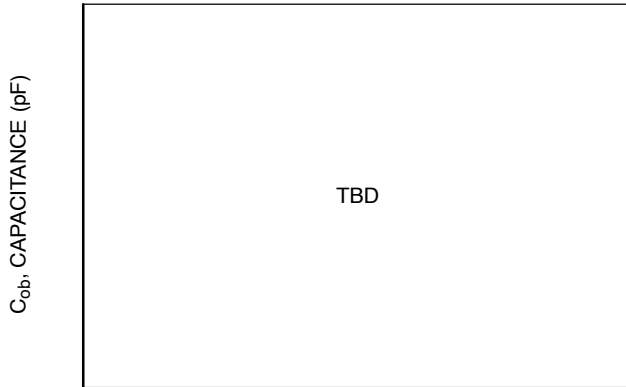
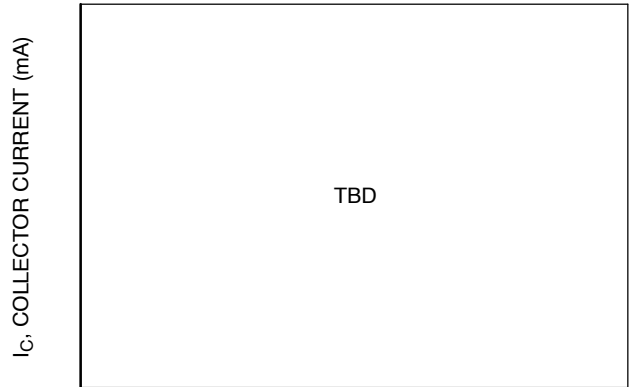


Figure 53. DC Current Gain



V_R , REVERSE BIAS VOLTAGE (VOLTS)

Figure 54. Output Capacitance



V_{in} , INPUT VOLTAGE (VOLTS)

Figure 55. Output Current versus Input Voltage

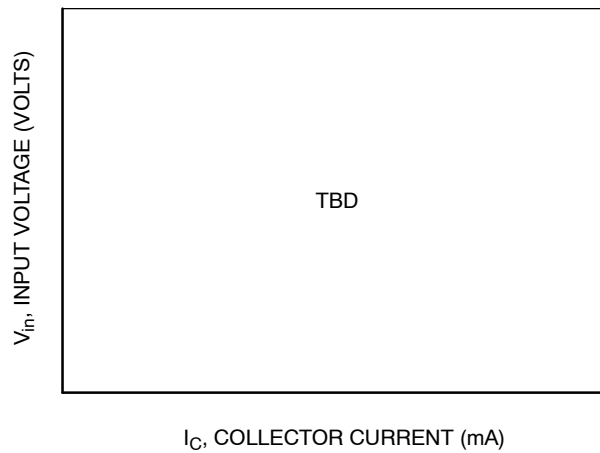


Figure 56. Input Voltage versus Output Current

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5235DW1T1G

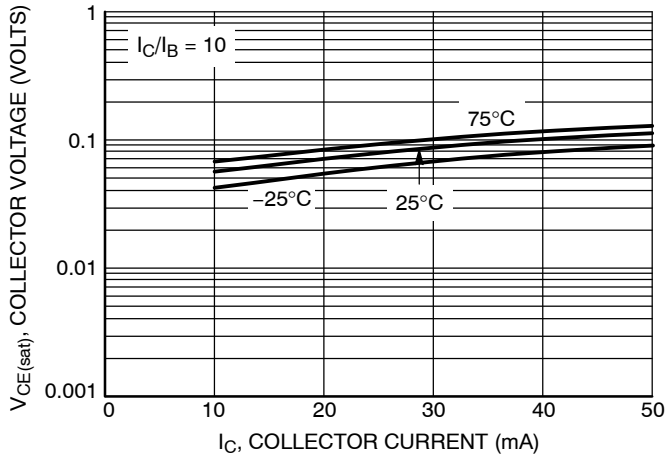


Figure 57. $V_{CE(sat)}$ versus I_C

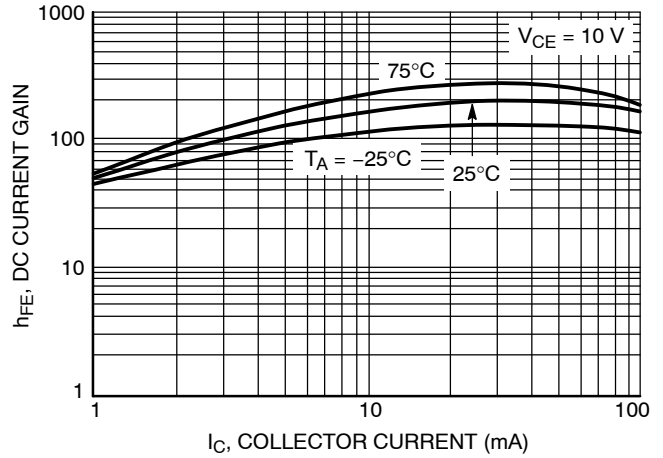


Figure 58. DC Current Gain

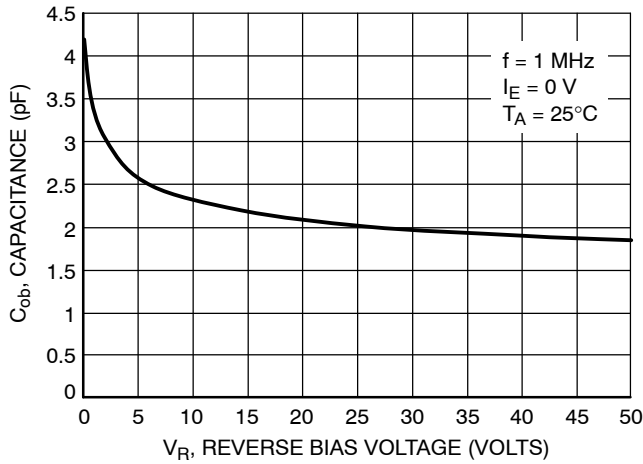


Figure 59. Output Capacitance

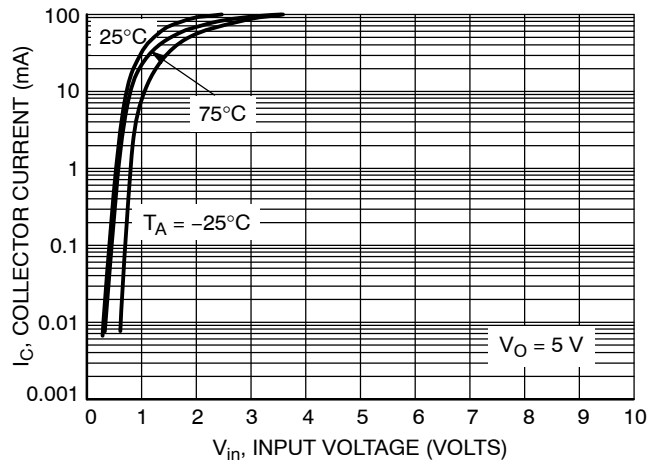


Figure 60. Output Current versus Input Voltage

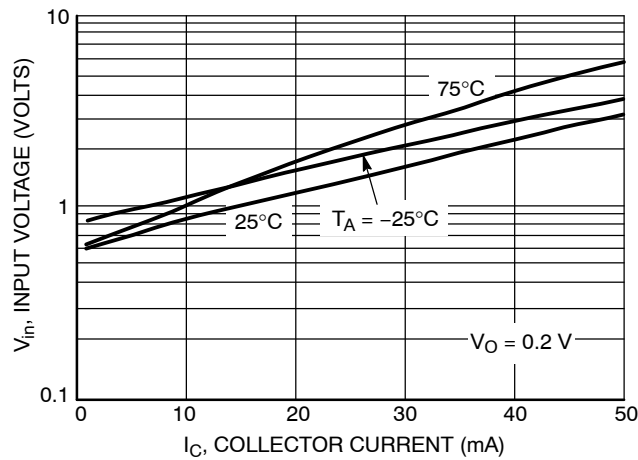


Figure 61. Input Voltage versus Output Current

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5236DW1T1G

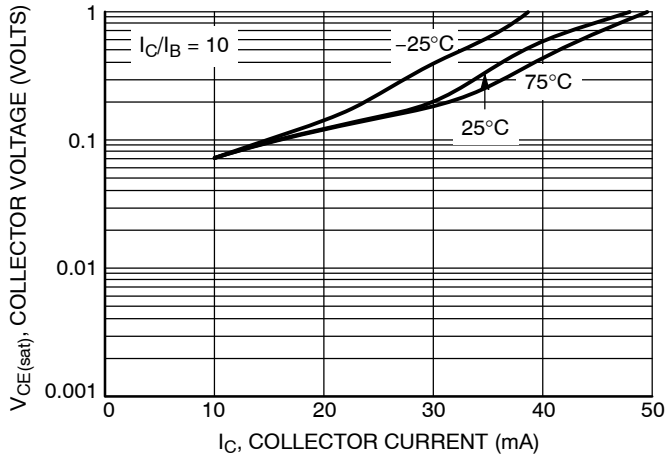


Figure 62. $V_{CE(sat)}$ versus I_C

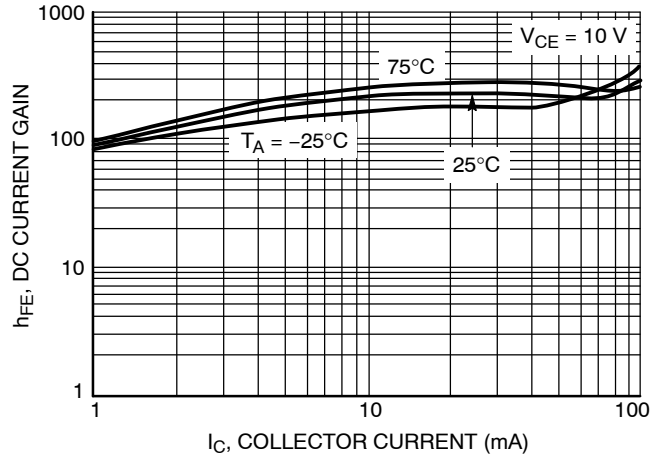


Figure 63. DC Current Gain

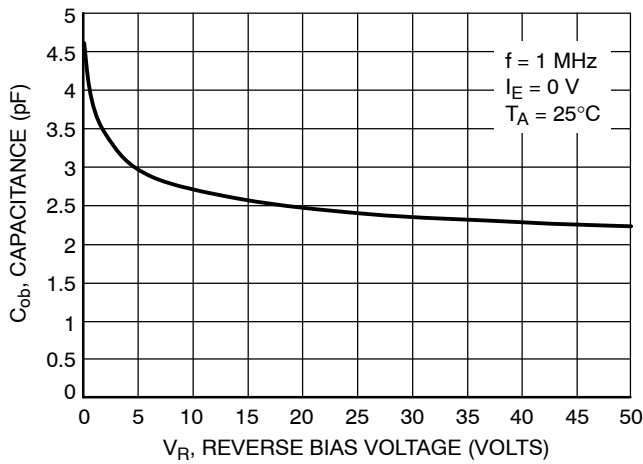


Figure 64. Output Capacitance

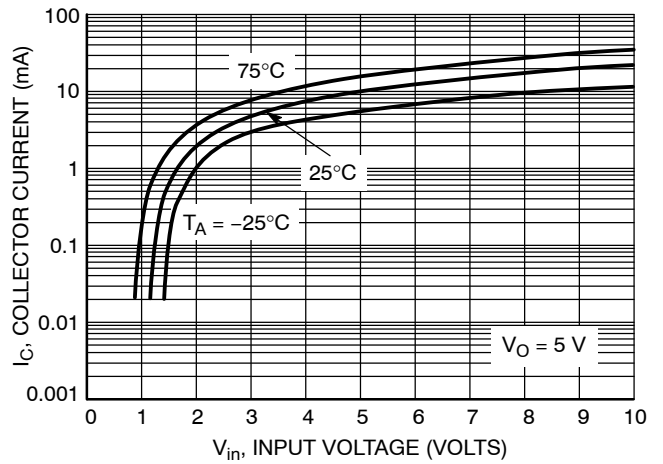


Figure 65. Output Current versus Input Voltage

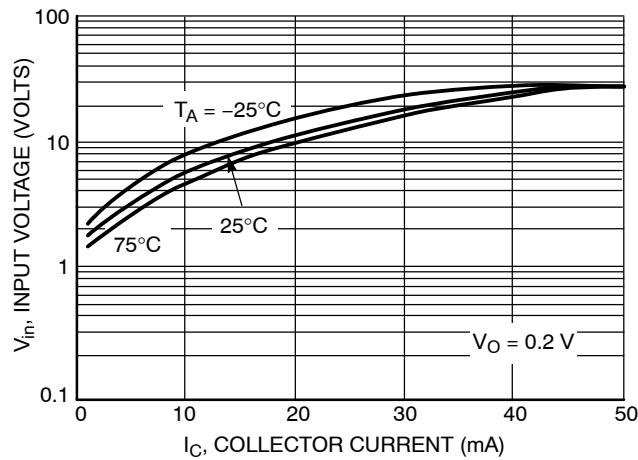


Figure 66. Input Voltage versus Output Current

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5237DW1T1G

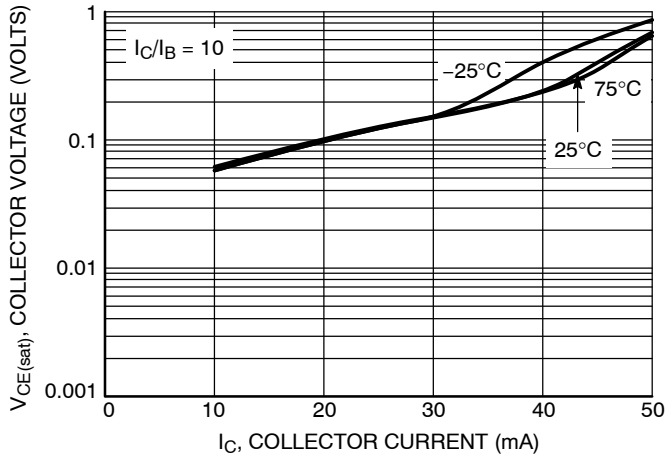


Figure 67. $V_{CE(sat)}$ versus I_C

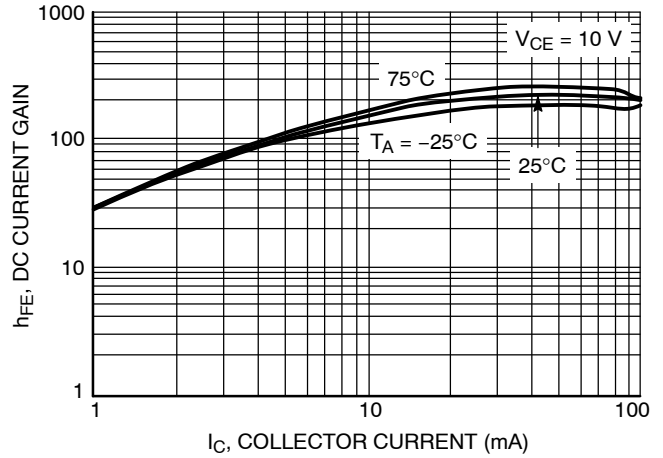


Figure 68. DC Current Gain

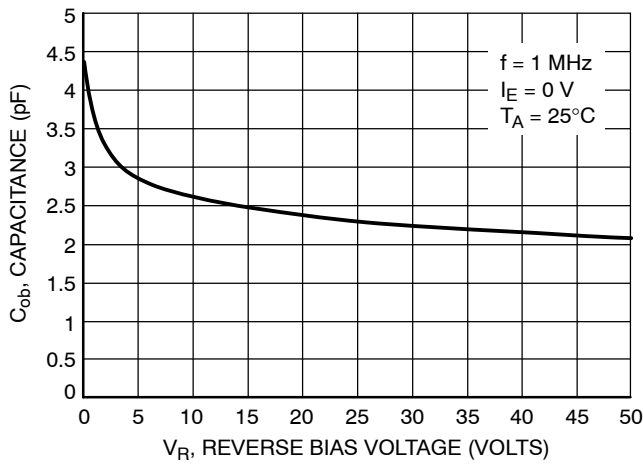


Figure 69. Output Capacitance

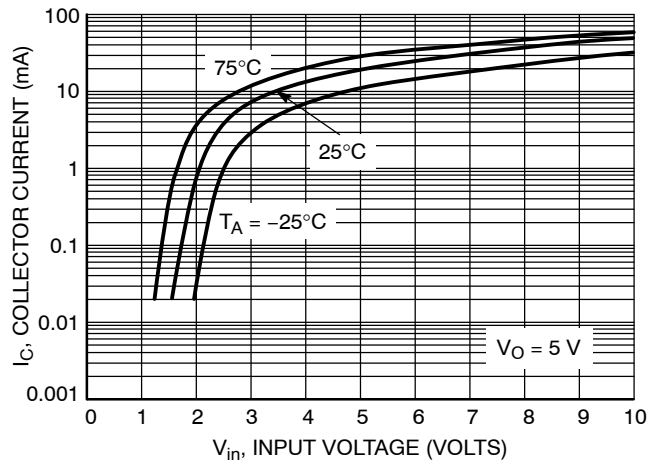


Figure 70. Output Current versus Input Voltage

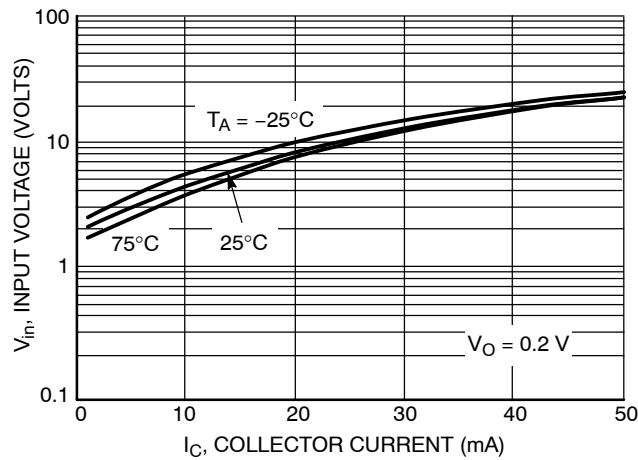
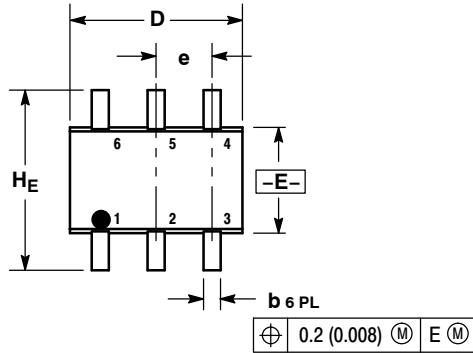


Figure 71. Input Voltage versus Output Current

MUN5211DW1T1G Series

PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363
CASE 419B-02
ISSUE W

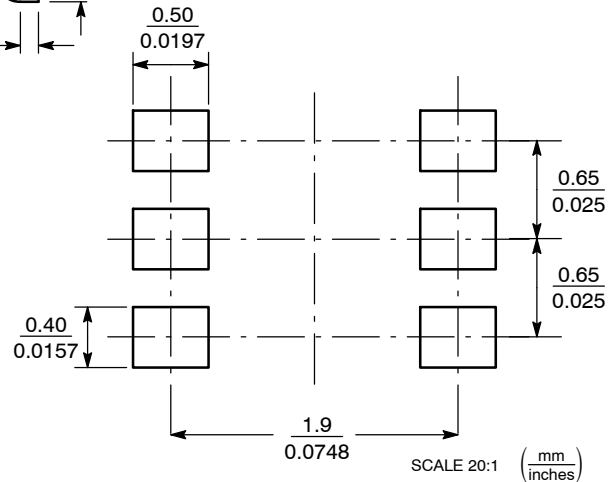


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.95	1.10	0.031	0.037	0.043
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.20 REF			0.008 REF		
b	0.10	0.21	0.30	0.004	0.008	0.012
C	0.10	0.14	0.25	0.004	0.005	0.010
D	1.80	2.00	2.20	0.070	0.078	0.086
E	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	2.00	2.10	2.20	0.078	0.082	0.086

- STYLE 1:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

SOLDERING FOOTPRINT*



SC-88/SC70-6/SOT-363

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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MUN5211DW1T1/D

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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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